



**Absolute Maximum Ratings** at  $T_j=25$  unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	$V_{DS}$	600	V
Gate-source voltage	$V_{GS}$	$\pm 30$	V
Continuous drain current <sup>1)</sup> , $T_C=25$ °C	$I_D$	47	A
Continuous drain current <sup>1)</sup> , $T_C=100$ °C		30	
Pulsed drain current <sup>2)</sup> , $T_C=25$ °C	$I_{D, pulse}$	141	A
Continuous diode forward current <sup>1)</sup> , $T_C=25$ °C	$I_S$	47	A
Diode pulsed current <sup>2)</sup> , $T_C=25$ °C	$I_{S, pulse}$	141	A
Power dissipation <sup>3)</sup> , $T_C=25$ °C	$P_D$	35	W
Single pulsed avalanche energy <sup>5)</sup>	$E_{AS}$	1000	mJ
MOSFET dv/dt ruggedness, $V_{DS}$	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS}$	dv/dt	50	V/ns
Operation and storage temperature	$T_{stg}, T_j$	-55 to 150	°C

**Thermal Characteristics**

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	R	3.6	°C/W
Thermal resistance, junction-ambient <sup>4)</sup>	R	62.5	°C/W

**Electrical Characteristics** at  $T_j=25$  unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	$BV_{DSS}$	600			V	$V_{GS}=0$ V, $I_D=1$ mA
		650				$V_{GS}=0$ V, $I_D=1$ mA, $T_j=150$ °C
Gate threshold voltage	$V_{GS(th)}$	3.0		4.5	V	$V_{DS}=V_{GS}$ , $I_D=1$ mA
Drain-source on-state resistance	$R_{DS(ON)}$		0.066	0.074		$V_{GS}=10$ V, $I_D=23.5$ A
			0.16			$V_{GS}=10$ V, $I_D=23.5$ A, $T_j=150$ °C
Gate-source leakage current	$I_{GSS}$			100	nA	$V_{GS}=30$ V
				-100		$V_{GS}=-30$ V
Drain-source leakage current	$I_{DSS}$			10	A	$V_{DS}=600$ V, $V_{GS}=0$ V
Gate resistance	$R_G$		8			Open drain

### Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	$C_{iss}$		3982		pF	$V_{GS}=0\text{ V}$ , $V_{DS}=50\text{ V}$ , Hz
Output capacitance	$C_{oss}$		354		pF	
Reverse transfer capacitance	$C_{rss}$		9.3		pF	
Turn-on delay time	$t_{d(on)}$		48.3		ns	$V_{GS}=10\text{ V}$ , $V_{DS}=400\text{ V}$ , $R_G$ $I_D=25\text{ A}$
Rise time	$t_r$		88		ns	
Turn-off delay time	$t_{d(off)}$		89.3		ns	
Fall time	$t_f$		7.2		ns	

### Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	$Q_g$		66.8		nC	$V_{GS}=10\text{ V}$ , $V_{DS}=400\text{ V}$ , $I_D=25\text{ A}$
Gate-source charge	$Q_{gs}$		24.4		nC	
Gate-drain charge	$Q_{gd}$		23.5		nC	
Gate plateau voltage	$V_{plateau}$		7.0		V	

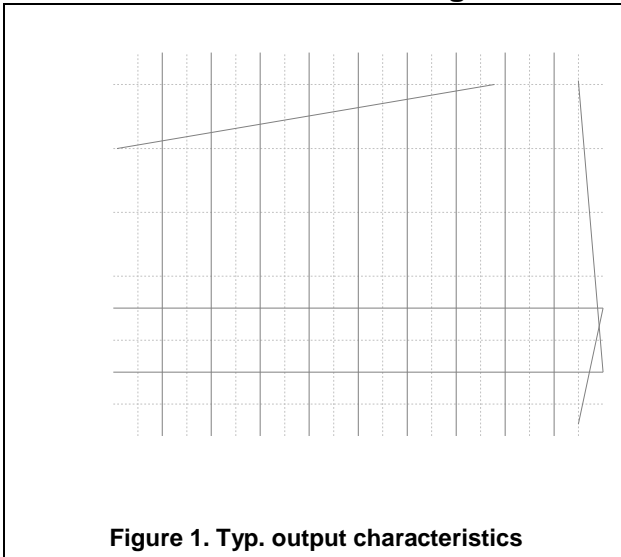
### Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	$V_{SD}$			1.4	V	$I_S=47\text{ A}$ , $V_{GS}=0\text{ V}$
Reverse recovery time	$t_{rr}$		158.3		ns	$I_S=25\text{ A}$ ,
Reverse recovery charge	$Q_{rr}$		1.1		uC	
Peak reverse recovery current	$I_{rrm}$		12.5		A	

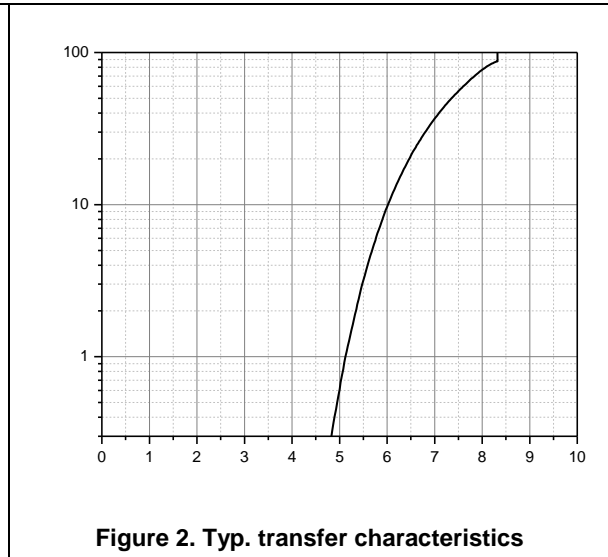
### Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3)  $P_d$  is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of  $R_{\theta}$  is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with  $T_a=25\text{ }^\circ\text{C}$ .
- 5)  $V_{DD}=100\text{ V}$ ,  $V_{GS}=10\text{ V}$ ,  $L=60\text{ mH}$ , starting  $T_j=25\text{ }^\circ\text{C}$ .

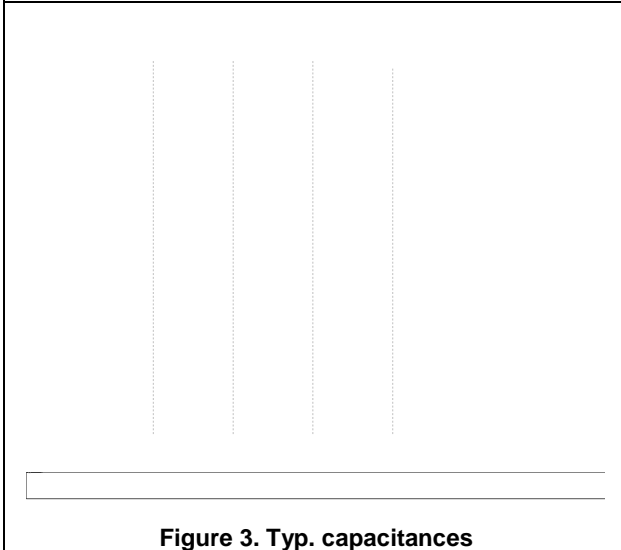
**Electrical Characteristics Diagrams**



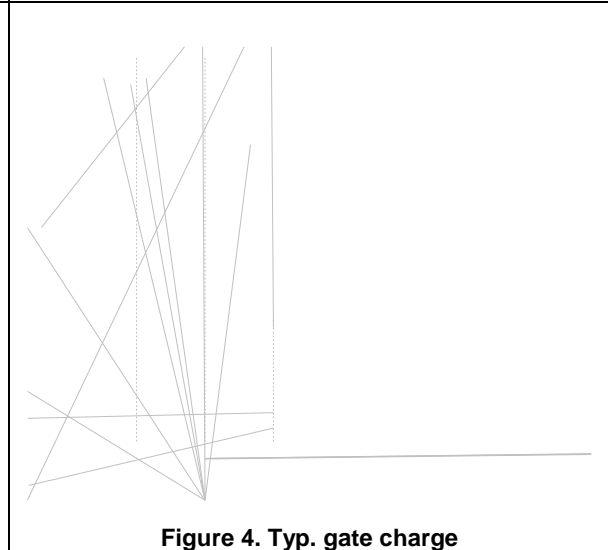
**Figure 1. Typ. output characteristics**



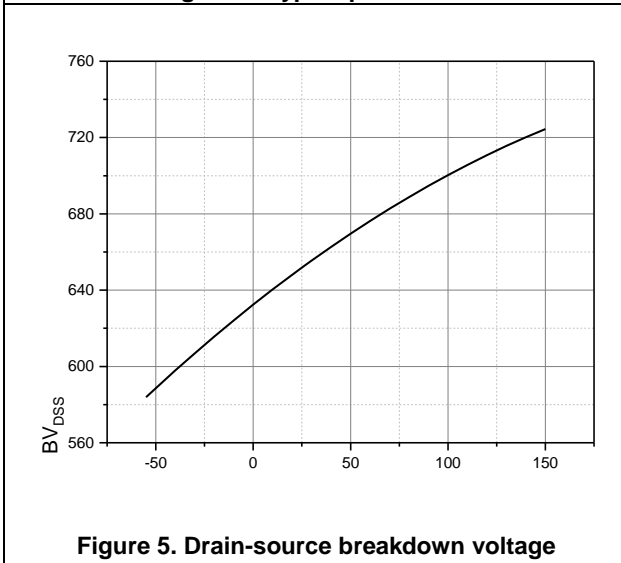
**Figure 2. Typ. transfer characteristics**



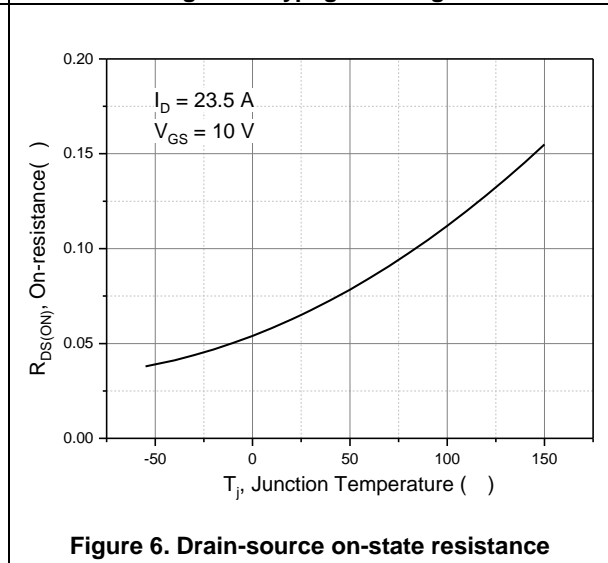
**Figure 3. Typ. capacitances**



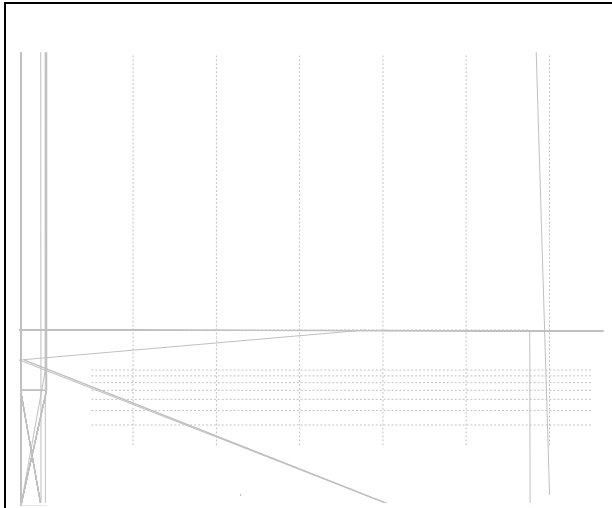
**Figure 4. Typ. gate charge**



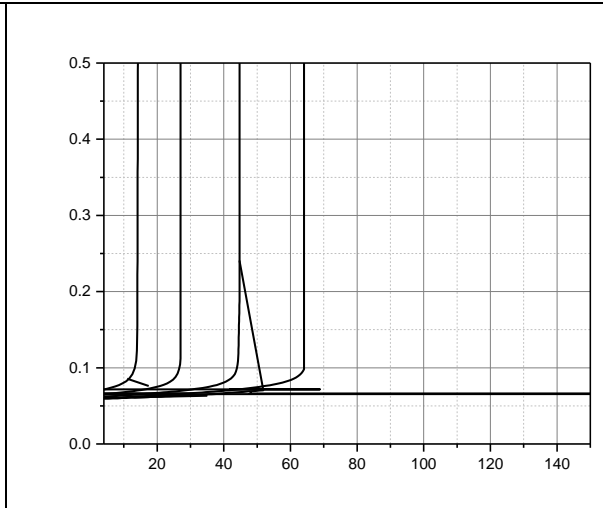
**Figure 5. Drain-source breakdown voltage**



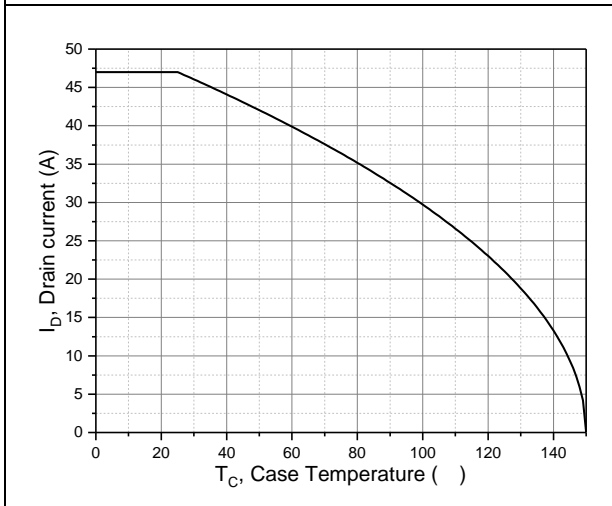
**Figure 6. Drain-source on-state resistance**



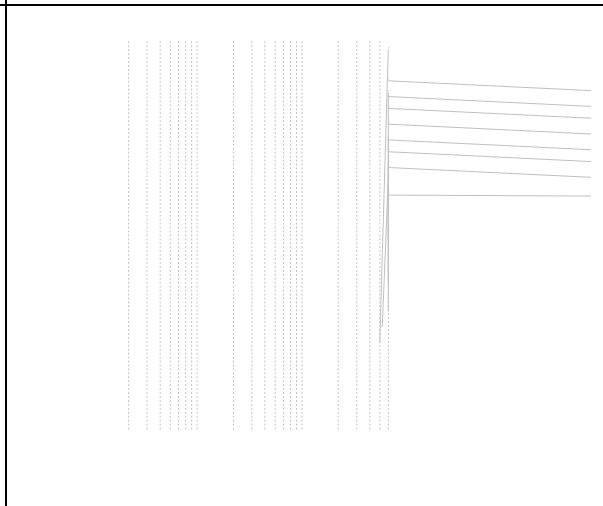
**Figure 7. Forward characteristic of body diode**



**Figure 8. Drain-source on-state resistance**

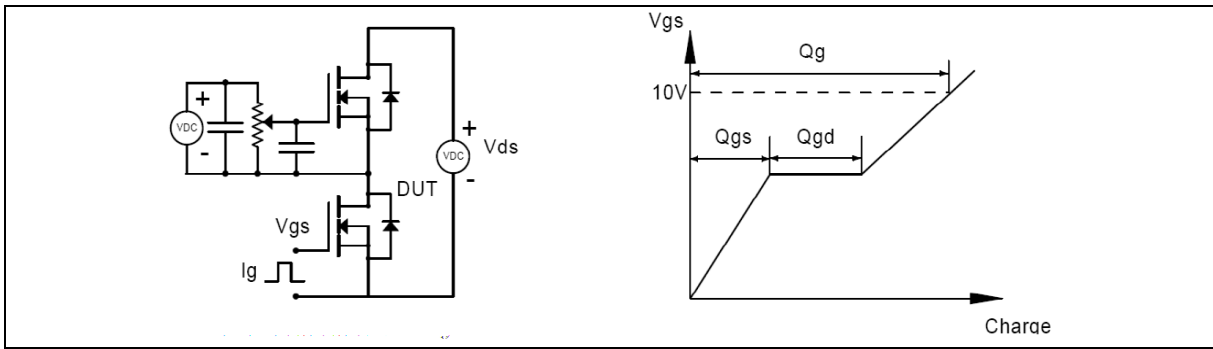


**Figure 9. Drain current**



**Figure 10. Safe operation area T<sub>C</sub>=25 °C**

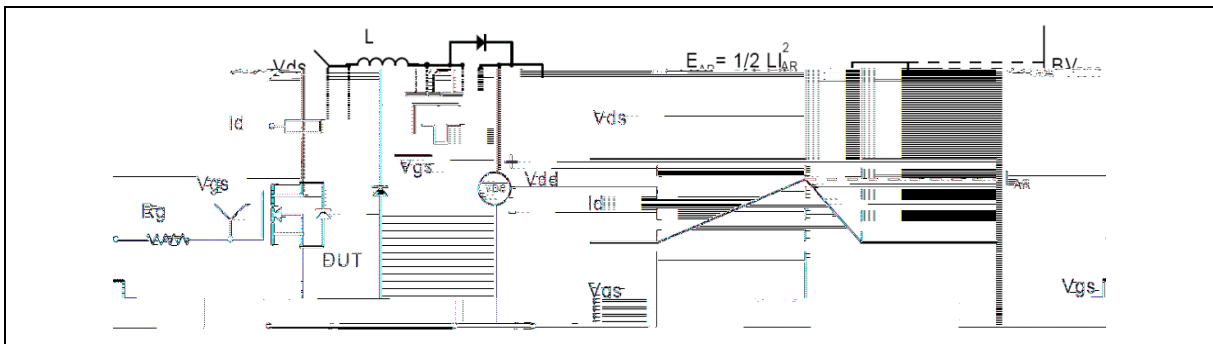
**Test circuits and waveforms**



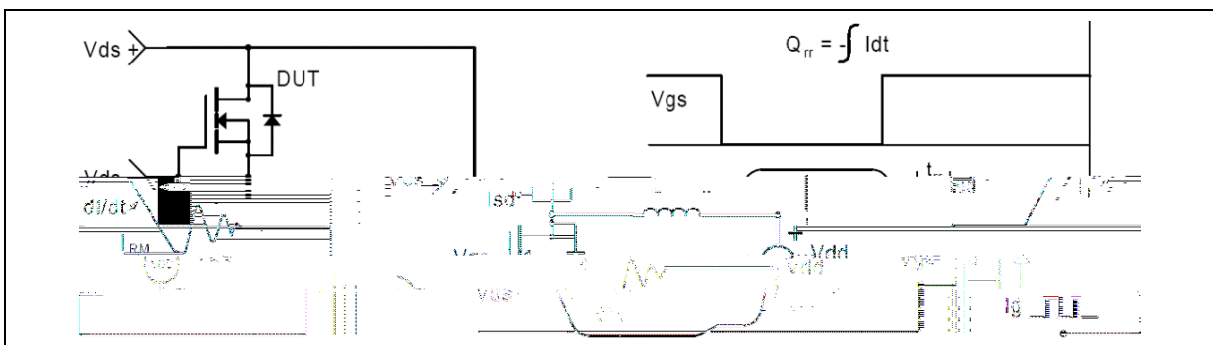
**Figure 1. Gate charge test circuit & waveform**



**Figure 2. Switching time test circuit & waveforms**



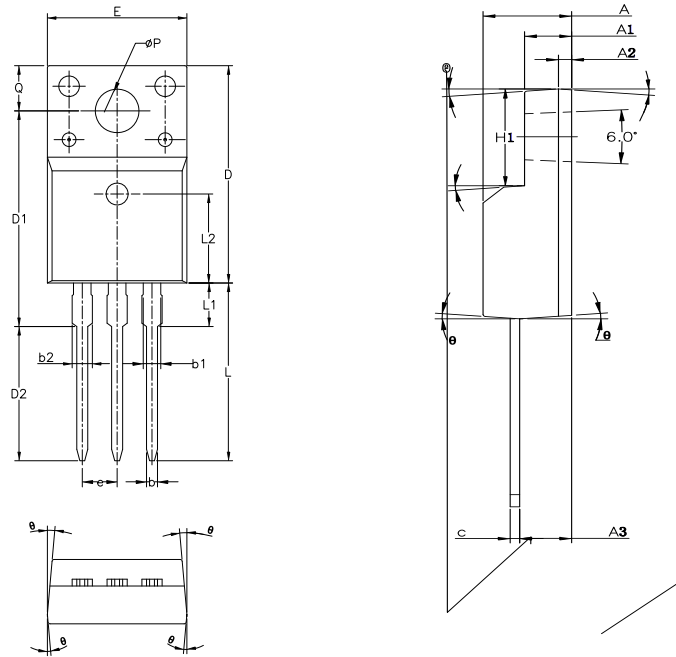
**Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms**



**Figure 4. Diode reverse recovery test circuit & waveforms**

## Package Information

**Package Information**



Symbol	mm		
	Min	Nom	Max
A	4.50	4.70	4.83
A1	2.34	2.54	2.74
A2	0.70 REF		
A3	2.56	2.76	2.93
b	0.70	-	0.90
b1	1.18	-	1.38
b2	-	-	1.47
c	0.45	0.50	0.60
D	15.67	15.87	16.07
D1	15.55	15.75	15.95
D2	9.60	9.80	10.00
E	9.96	10.16	10.36
e	2.54 BSC		
H1	6.48	6.68	6.88
L	12.68	12.98	13.28
L1	-	-	3.50
L2	6.50 REF		
	3.08	3.18	3.28
Q	3.20	-	3.40
	1°	3°	5°

Version 2: TO220F-J outline dimension



**Ordering Information**

Package Type	Units/ Tube	Tubes / Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO220F-C	50	20	1000	6	6000
TO220F-J	50	20	1000	5	5000

**Product Information**

Product	Package	Pb Free	RoHS	Halogen Free
OSG60R074FSZF	TO220F	yes	yes	yes

